

**Silicon NPN Power Transistors**

**2SC1161**

**DESCRIPTION**

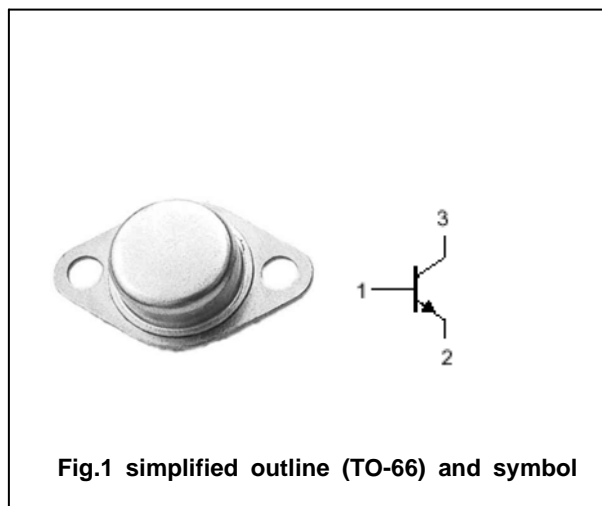
- With TO-66 package
- Low collector saturation voltage

**APPLICATIONS**

- For low frequency high voltage power amplifier TV vertical deflection output applications.

**PINNING(see Fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



**Absolute maximum ratings(Ta=°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	200	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	120	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	6	V
I <sub>C</sub>	Collector current		1	A
P <sub>D</sub>	Total power dissipation	T <sub>C</sub> =25°C	15	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =50mA ; I <sub>B</sub> =0	120			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA ; I <sub>C</sub> =0	6			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =500mA; I <sub>B</sub> =50mA			1.5	V
V <sub>BE sat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =500mA; I <sub>B</sub> =50mA			2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =120V; I <sub>E</sub> =0			1.0	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =6V; I <sub>C</sub> =0			1.0	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =200mA ; V <sub>CE</sub> =5V	30		200	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =200mA ; V <sub>CE</sub> =10V	5			MHz

PACKAGE OUTLINE

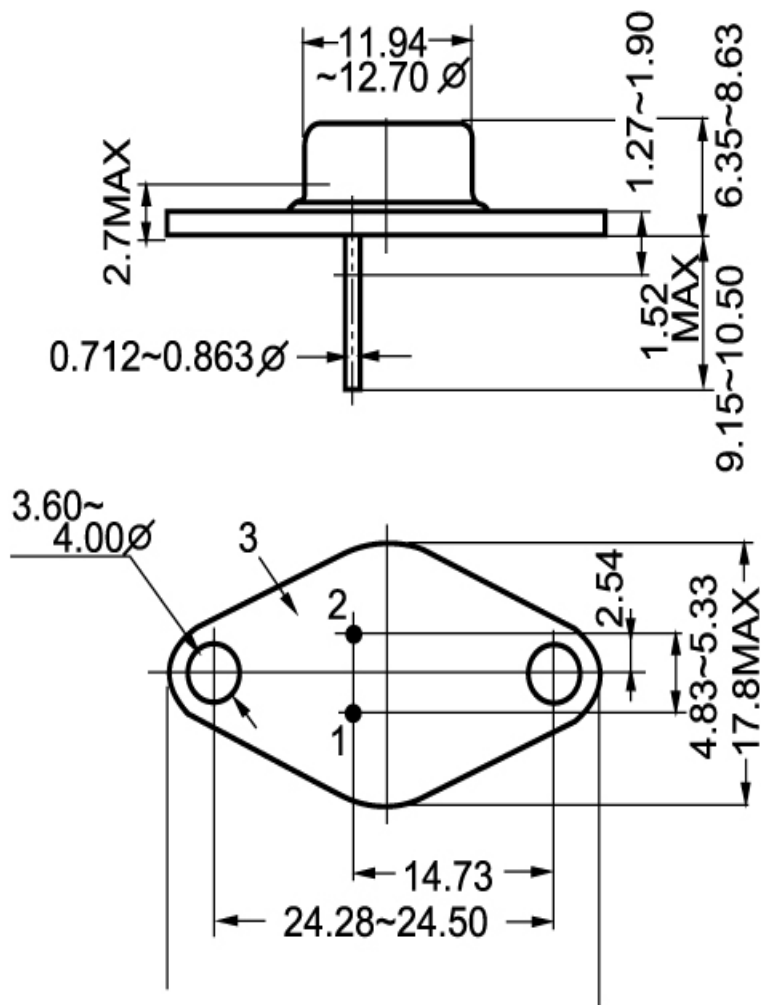


Fig.2 outline dimensions